

IN THE CLAIMS

1. (Currently Amended) In a transistor device, a gate dielectric comprising:
 - a first layer comprising hafnium oxide; and
 - a second layer, ~~adjacent to~~ under the first layer, comprising zirconium oxide.
2. (Currently Amended) The transistor device of claim 1, wherein the gate dielectric is present between a semiconductor substrate and a gate electrode of the transistor device, and wherein the hafnium oxide is ~~adjacent to~~ under the gate electrode.
3. (Currently Amended) The transistor device of claim 2, wherein the gate dielectric further comprises a third layer, ~~adjacent to~~ under the first layer, comprising a second metal oxide different from hafnium oxide.

4-8. (Previously Cancelled)

9. (Currently Amended) The transistor device of claim 1, wherein the gate dielectric is present between a semiconductor substrate and a gate electrode of the transistor device, and wherein the zirconium oxide is ~~adjacent to~~ over the semiconductor substrate.

10-25. (Previously Cancelled)

26. (Currently Amended) A transistor device, comprising:
 - a semiconductor substrate having a source, a drain, and a channel between the source and the drain;
 - a gate electrode over the channel; and
 - a gate dielectric comprising a first layer of substantially pure hafnium oxide and a second layer, ~~adjacent to~~ under the first layer, wherein the second layer comprises zirconium oxide.

27. (Currently Amended) The transistor device of claim 26, wherein the gate dielectric further comprises a third layer of the substantially pure metal oxide, wherein the third layer is adjacent to under the semiconductor substrate over the channel, the first layer is over the third layer, and the second layer is over the first layer.

28. (Previously Cancelled)

29. (Original) The transistor device of claim 26, wherein the second layer is deposited by ALD.

30-31. (Previously Cancelled)